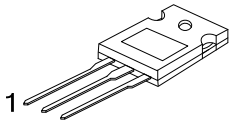
400V, 23A N-CHANNEL POWER MOSFET



TO-247

■ DESCRIPTION

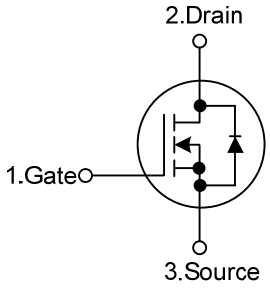
The UTC **20N40** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **20N40** is generally applied in high efficiency switch mode power supplies.

■ FEATURES

* $R_{DS(ON)}$=0.2Ω @ V_{GS}=10V,I_D=11.5A
* Low Gate Charge (Typical 46nC)
* Low C_{RSS} (Typical 25pF)
* High Switching Speed

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
20N40L-T47-T	20N40G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

20N40L-T47-T (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube (2) T47: TO-247 (3) G: Halogen Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	400	V
Gate-Source Voltage			V_{GSS}	±30	V
Drain Current	Continuous	T_C=25°C	I_D	23	A
		T_C=100°C		13.8	A
	Pulsed (Note 2)		I_{DM}	92	A
Avalanche Current (Note 2)			I_{AR}	23	A
Avalanche Energy	Single Pulsed (Note 3)		E_{AS}	1190	mJ
	Repetitive (Note 2)		E_{AR}	23.5	mJ
Peak Diode Recovery dv/dt (Note 4)			dv/dt	4.5	V/ns
Power Dissipation (T_C=25°C)			P_D	235	W
Derate above 25°C				1.8	W/°C
Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 4.5mH, I_{AS} = 23A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 23A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

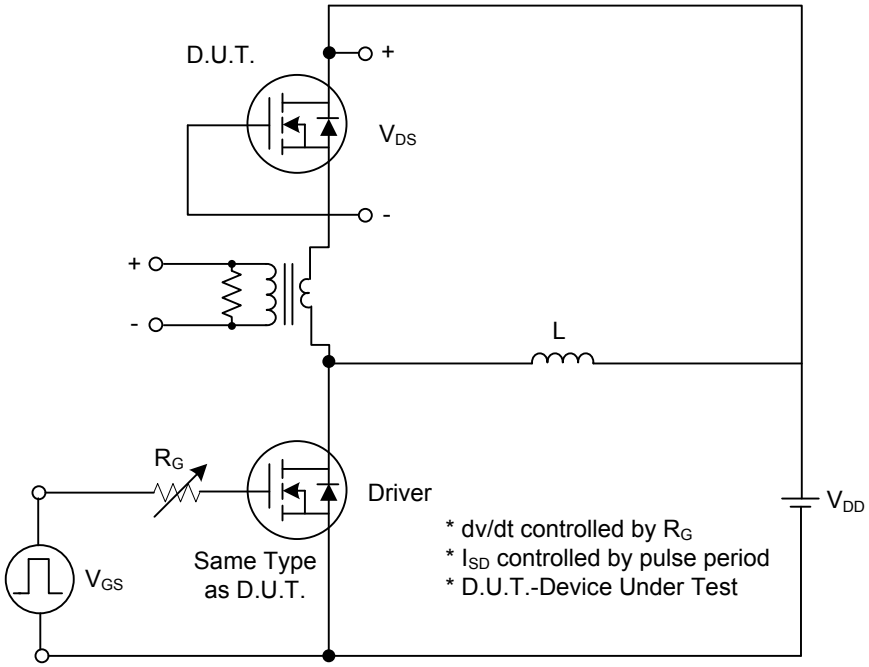
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	40	°C/W
Junction to Case	θ_{JC}	0.53	°C/W

■ ELECTRICAL CHARACTERISTICS

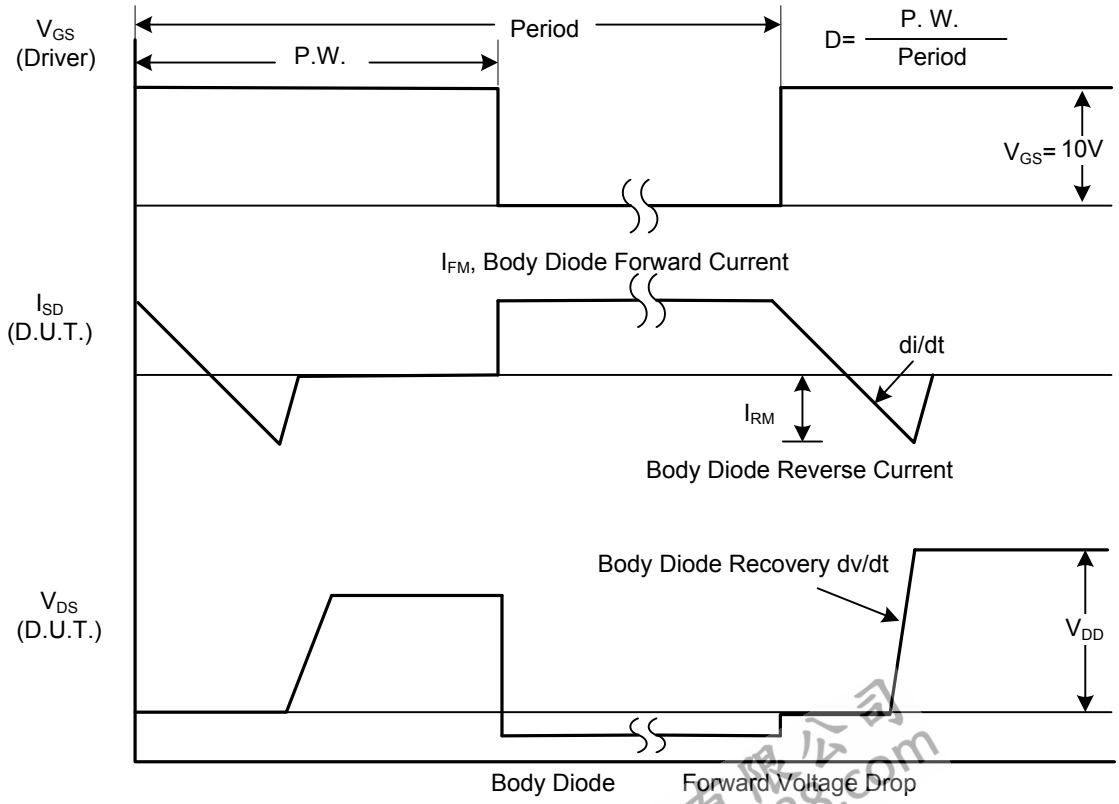
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	400			V
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	Reference to 25°C, I_D=250μA		0.5		V/°C
Drain-Source Leakage Current		I_{DSS}	V_{DS}=400V, V_{GS}=0V			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=11.5A		0.15	0.2	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		2280	3030	pF
Output Capacitance		C_{OSS}			370	490	pF
Reverse Transfer Capacitance		C_{RSS}			25	38	pF
SWITCHING PARAMETERS							
Total Gate Charge at 10V		$Q_{G(TOT)}$	V_{DS}=320V, I_D=23A (Note 1, 2)		46	60	nC
Gate to Source Charge		Q_{GS}			13		nC
Gate to Drain Charge		Q_{GD}			18		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DS}=200V, I_D=23A, R_G=25Ω (Note 1, 2)		40	90	ns
Rise Time		t_R			92	195	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			120	250	ns
Fall-Time		t_F			75	160	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				23	A
Maximum Body-Diode Pulsed Current		I_{SM}				92	A
Drain-Source Diode Forward Voltage		V_{SD}	I_{SD}=23A, V_{GS}=0V			1.5	V
Body Diode Reverse Recovery Time		t_{rr}	I_{SD}=23A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		110		ns
Body Diode Reverse Recovery Charge		Q_{RR}			0.3		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially Independent of Operating Temperature Typical Characteristics

■ TEST CIRCUITS AND WAVEFORMS

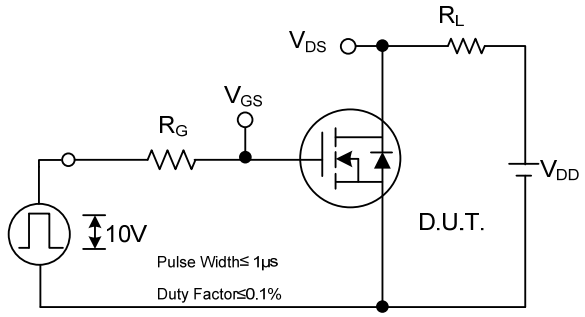


Peak Diode Recovery dv/dt Test Circuit

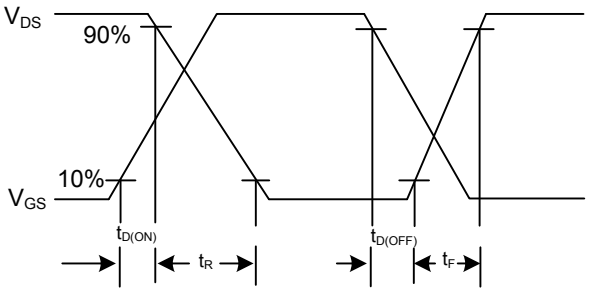


Peak Diode Recovery dv/dt Waveforms

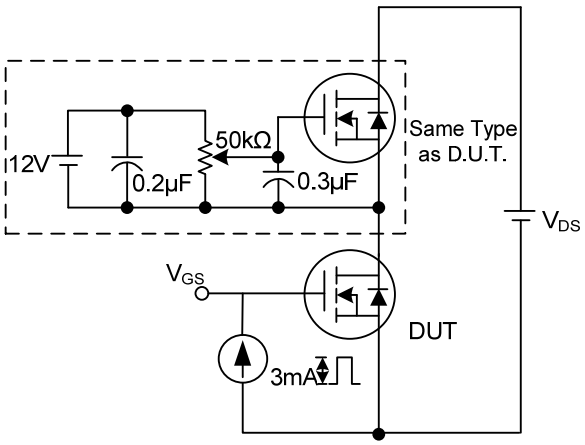
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



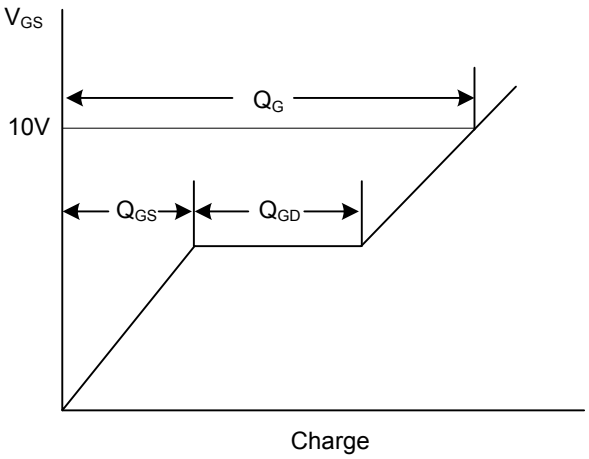
Switching Test Circuit



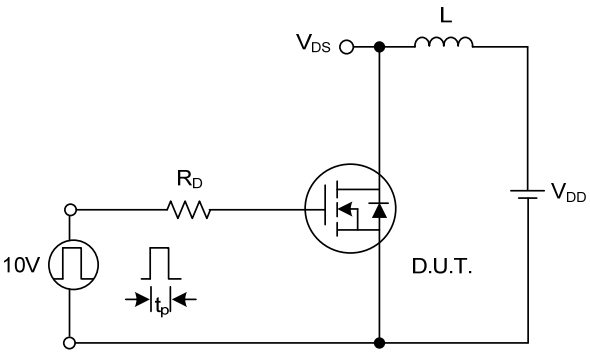
Switching Waveforms



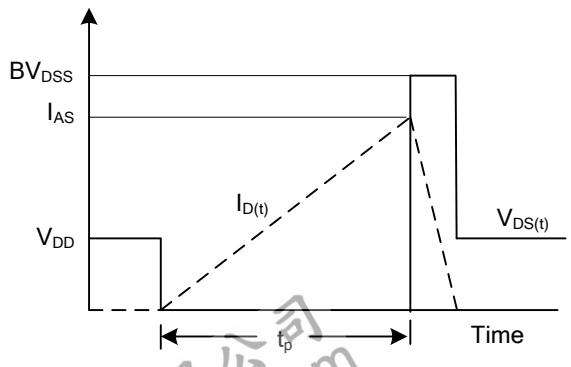
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms